GWIT
Guang Wei Integration Technology

GF85M3HUF

Fast Recovery Epitaxial Diode(FRED)

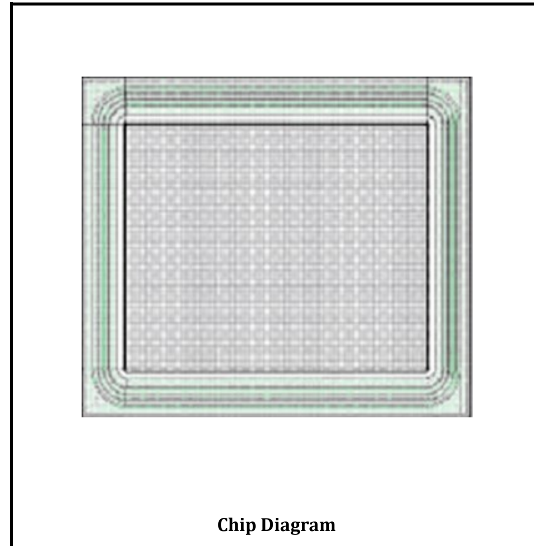
PRODUCT FEATURES

◆Ultrafast Recovery Time
◆Soft Recovery Characteristics
◆Low Forward Voltage
◆Low Leakage Current
◆Low Recovery Loss

Applications (not limited to)

◆Freewheeling, Snubber,Clamp
◆Snubber Diode
◆Switch Power Supplies
◆Motor control
◆Inverters,Converters

Items	Description
Wafer Size	5 Inch
Gross Die	2300 EA
Top Metal	Al
Back Metal	Ag
Dimensions	um
Chip Size（A）	2160μm * 2160μm
Pad Size（B）	1750μm * 1750μm
Wafer Thickness（D）	260±20μm
Scribe Line width（E）	50 μm
Bonding Wire	Al, 15mil*1



Chip Diagram

Absolute Maximum ratings（T_a=25℃）

Parameter	Symbol	Value	Units
DC Blocking Voltage	V_{RRM}	300	V
Average Rectified Forward Current	I_{FAV}	10	A
Nonrepetitive Peak Surge Current@8.3mS	I_{FSM}	150	A
Operating Junction Temperature	T_J	175	℃
Storage Temperature	T_{STG}	- 55~150	℃

Electrical specification（T_a=25℃）

Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
Reverse Breakdown Voltage	V_{BR}	I_R=50μA	300	370	-	V
Forward Voltage	V_F	I_F=10A, T_a=25℃	-	1.10	1.30	V
		I_F=10A,T_a=125℃	-	0.95	1.20	V
Reverse Leakage Current	I_R	V_R=300V,T_a=25℃	-	-	2	μA
		V_R=300V, T_a=125℃	-	-	50	μA
Reverse Recovery Time	T_{rr}	I_F=0.5A, I_R=1A, I_{rr}=0.25A	-	17	25	ns
		I_F=1A, V_R=30V, ,di/dt=-200A/us	-	20	-	ns

Remark：
1.Customer should obtain the latest version of datasheet before placing order, and verify the relevant information.
2.Cutting damage and chipping area can't beyond scribe line in given size range.
3.Testing system of Trr could be different, customer might take secondary test to evaluate if necessary.
4.Customer might choose the bonding wire material and diameter according to acutal sitatuation ,while no less than our recommendation.